

2. Repair Description (1/2)

SYSTEM			Remark
MC NAME&SREAL	NAME	NSR-2205i11D	
	SERIAL		
BASIC VERSION	MCSV BASIC	2.31D	
OPTION VERSION	OCS OPTION	2.31	
MAINTENANCE SYSTEM	MAINTENANCE SYSTEM	2.31	
UNIT SOFT VER	RETICLE LOADER	NA	
	WAFER STAGE	NA	
	OPERATION PANEL	NA	
	WAFER LOADER	NA	
	WAFER SENSOR	NA	
	LENS CONTROLLER	NA	
	RETICLE STAGE	NA	
MAIN COMPUTER	SYSTEM	VAX station	VAX4000 90A
	Hard disk	Yes	include Software
	DISK Drive	DAT Dape	

2. Repair Description (2/2)

UNIT STATUS	ILLUMINATION TYPE	Shrinc Type : No	1.75Kw
		Revolver Type : No	NA
	WAFER STAGE	Chuck Type : 8 inch (Notch)	
		Screw Type : Ballscrew	
	RETICLE ALIGNMENT	SRA , VRA	
	Reticle Microscope	FIX	
	WAFER ALIGNMENT	LSA , FIA	
	AUTO FOCUS	Multi	FC2
	WAFER LOADER	Wafer Size : 8inch Notch	
		Loader Type : Type 2	
		OF Type : 8inch Notch	
		Flatzone : 6C	
		In-Line : Right	No Option
		Cassette : Left,Right	
	Control Rack Position	Right	
	RETICLE LOADER	Reticle Size : 6"	
		Reticle Type : Library	1 Library(10ea/etch)
	PPD	No	
	BARCODE SYSTEM	Reticle	
	VINTAGE	1995.Sep.	
	CHAMBER TYPE	Asahi Kogyosha Co.,LTD.	N2B-B

3. Source Inspection

No	Inspection Item	Check
1	Exposure Power	
2	Illumination Uniformity	
3	Exposure Stability	
4	Stage Movement	
5	Wafer Loading/Unloading	
6	Reticle Exchange Operation	
7	Monitor Test Shot	
8	Error / Interlock Status	
9	System Initialization	

4. Acceptance Test Sheet

No	Item	Specification	Result				Remark
1	Exposure Power	600mW/cm ² or more	768 mW/cm ²				
2	Illumination Uniformity	Within ± 1.5%	0.994%				
3	FIA Telecem	±3 mrad	X :-1.499 mrad		Y : -0.508mrad		
	FIA Focus	±2 μm	X : -0.590 μm		Y : 0.518 μm		
4	LSA Telecem	±3 mrad	X :-1.096mrad		Y :-1.966mrad		
	LSA Focus	±2 μm	X : 1.387 μm		Y : 1.613 μm		
5	Intergrated Exposure Stability	Within ±1.0%	100:0.5%		200:0.5%		
			400:0.5%		800:0.5%		
6	Wafer Holder Flatness	Within 2.5 μm / 200mm	Max - Min		1.480 μm		
			Max		0.340 μm		
7	Chip Leveling	Within ±5 μ rad	X : 1.230 μ rad		Y : -3.915 μ rad		
			R : -3.638 μ rad		P : -1.898 μ rad		
8	Auto Focus Repeatanility	Within 0.2 μm	0.037 μm				
9	Reticle Blind Setting Accuacy	+ 0.4 to + 0.8mm (on reticle)	Xp		0.65mm		
			Xm		0.6mm		
			Yp		0.65mm		
			Ym		0.55mm		
10	Reticle Rotation	Absolute value Within ±0.02 μm OF target value Repeatability Within 0.02 μm	Absolute value				
			-0.005um				
			Repeatability				
			0.001um				
11	Array Orthogonality	Within ±0.1 sec Within ±0.48μrad	0.010sec				
			ORTM: -0.085 μ rad		ORTM90: 0.182μrad		
12	Stepping Precision	Within ±0.050 μm (3 σ)	3 Sigma				
			x	0.033 μm	y	0.026 μm	
13	Lens Distortion (Option)	Within ±0.060 μm	Max				
			x	0.042 μm	y	0.038 μm	
			Min				
			x	'-0.024 μm	y	-0.038 μm	
14	Overlay-LSA	3 σ ≤0.065 μm	x	0.044 μm	y	0.042 μm	
15	Overlay-FIA	3 σ ≤0.065 μm	x	0.041 μm	y	0.040 μm	
16	WL Repeatability	Within 15 μm (3 σ)	X:0.971 μm Y:1.732 μm T:1.898 μm				
17	Cycle test	100pcs/1 Carrier	O.K				
18	Field Inclination	UL-LR & UR-LL ≤ ±0.2 μm	UL-LR:0.055, UR-LL:-0.073				